

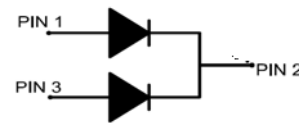
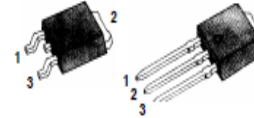


TO 252,251 SCHOTTKY BARRIER RECTIFIERS

MBR10100CT

FEATURES

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- Low Power Loss, High Efficiency
- High Surge Capability
- High Current Capability and Low Forward Voltage Drop
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications



Dimensions in millimeters and (inches)

ELECTRICAL CHARACTERISTICS (Tamb=25°C)

Characteristic	Symbol	MBR10100CT	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	100	V
Working Peak Reverse Voltage	V_{RWM}		
DC Blocking Voltage	V_R		
Average Rectified Output Current	I_C	10	A
Maximum Instantaneous Forward Voltage @ $I_F = 10A, T_c = 25^\circ C$ @ $I_F = 10A, T_c = 125^\circ C$ @ $I_F = 20A, T_c = 25^\circ C$ @ $I_F = 20A, T_c = 125^\circ C$	V_F	0.8 0.85 0.85 0.75	V
Peak Reverse Current @ $T_c = 25^\circ C$ at Rated DC Blocking Voltage @ $T_c = 125^\circ C$	I_R	10 200	μA
Operating and Storage Temperature Range	T_j, T_{stg}	-55 to +150	$^\circ C$

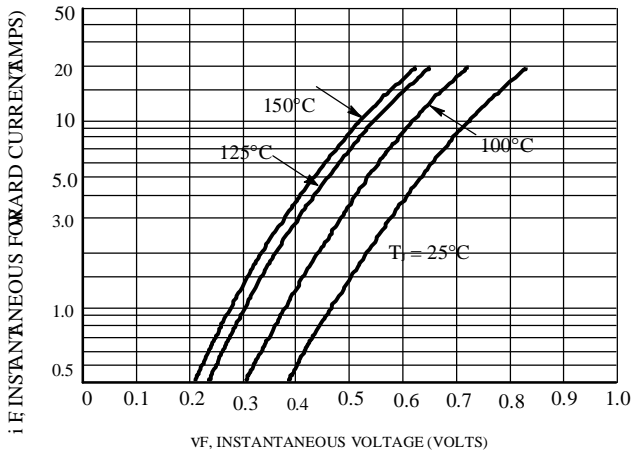


Figure 1. Typical Forward Voltage

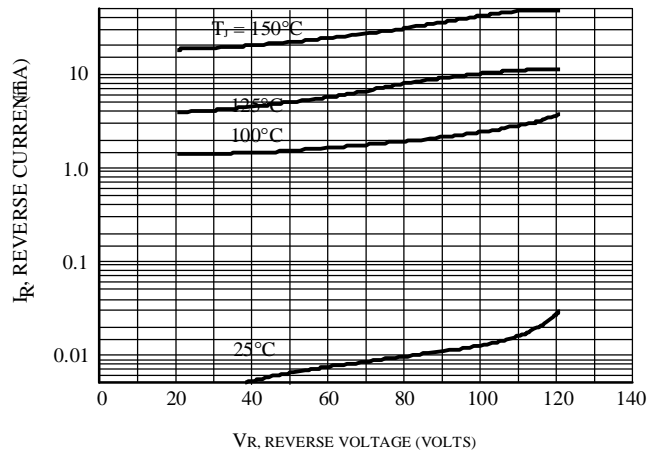


Figure 2. Typical Reverse Current

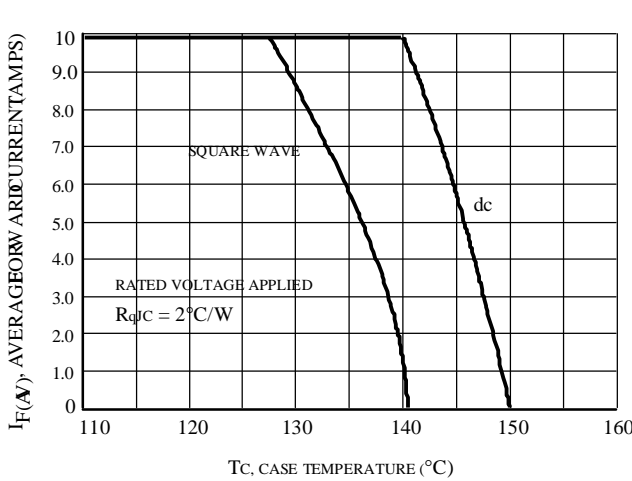


Figure 3. Current Derating, Case

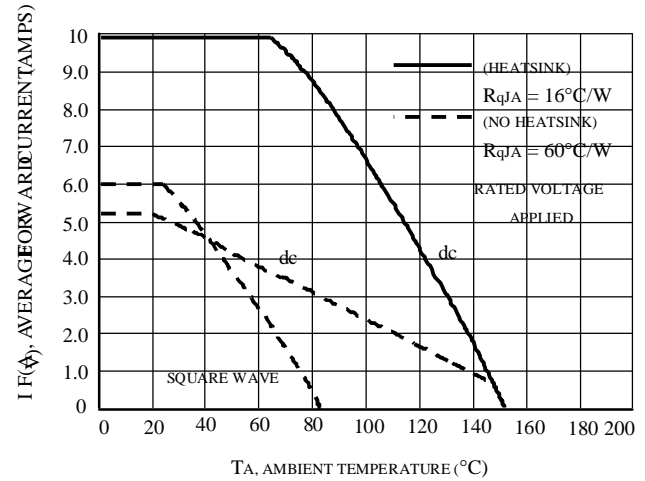


Figure 4. Current Derating, Ambient

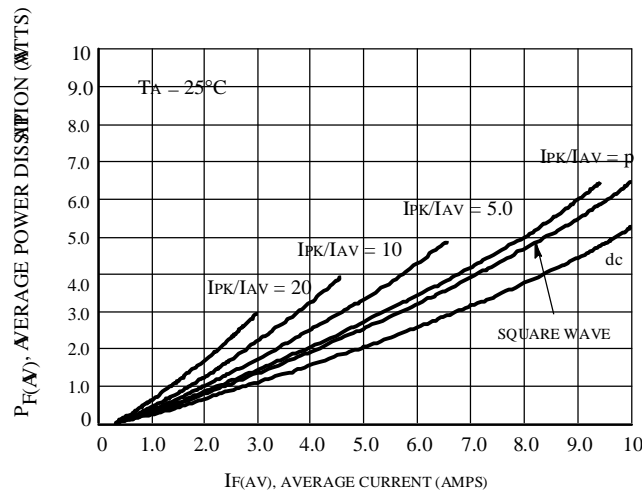
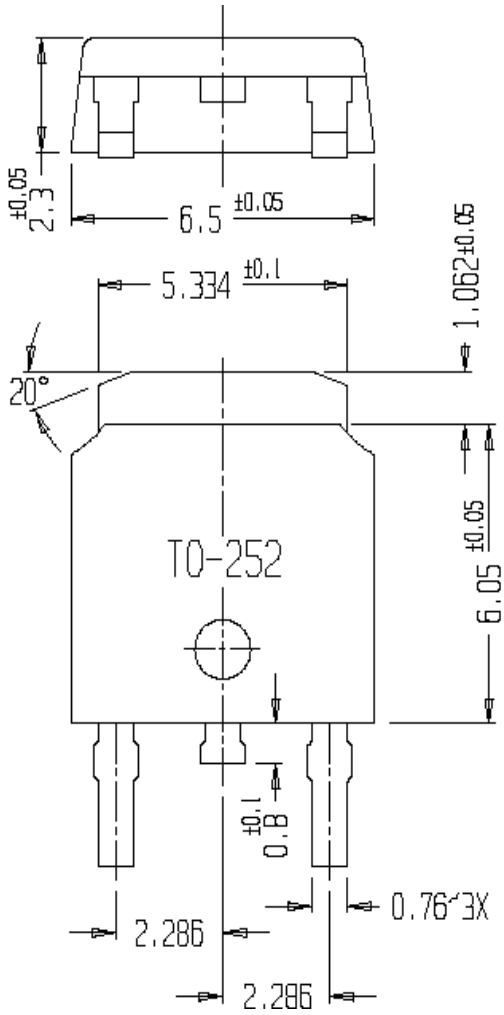
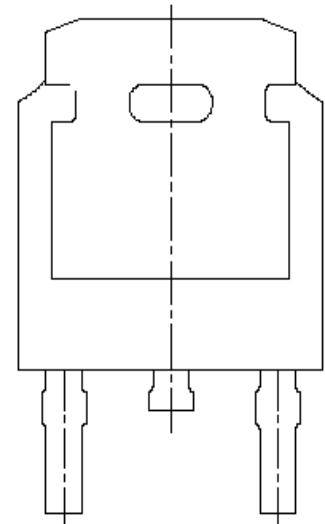
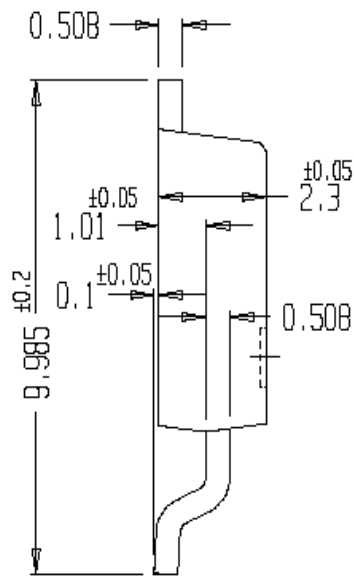


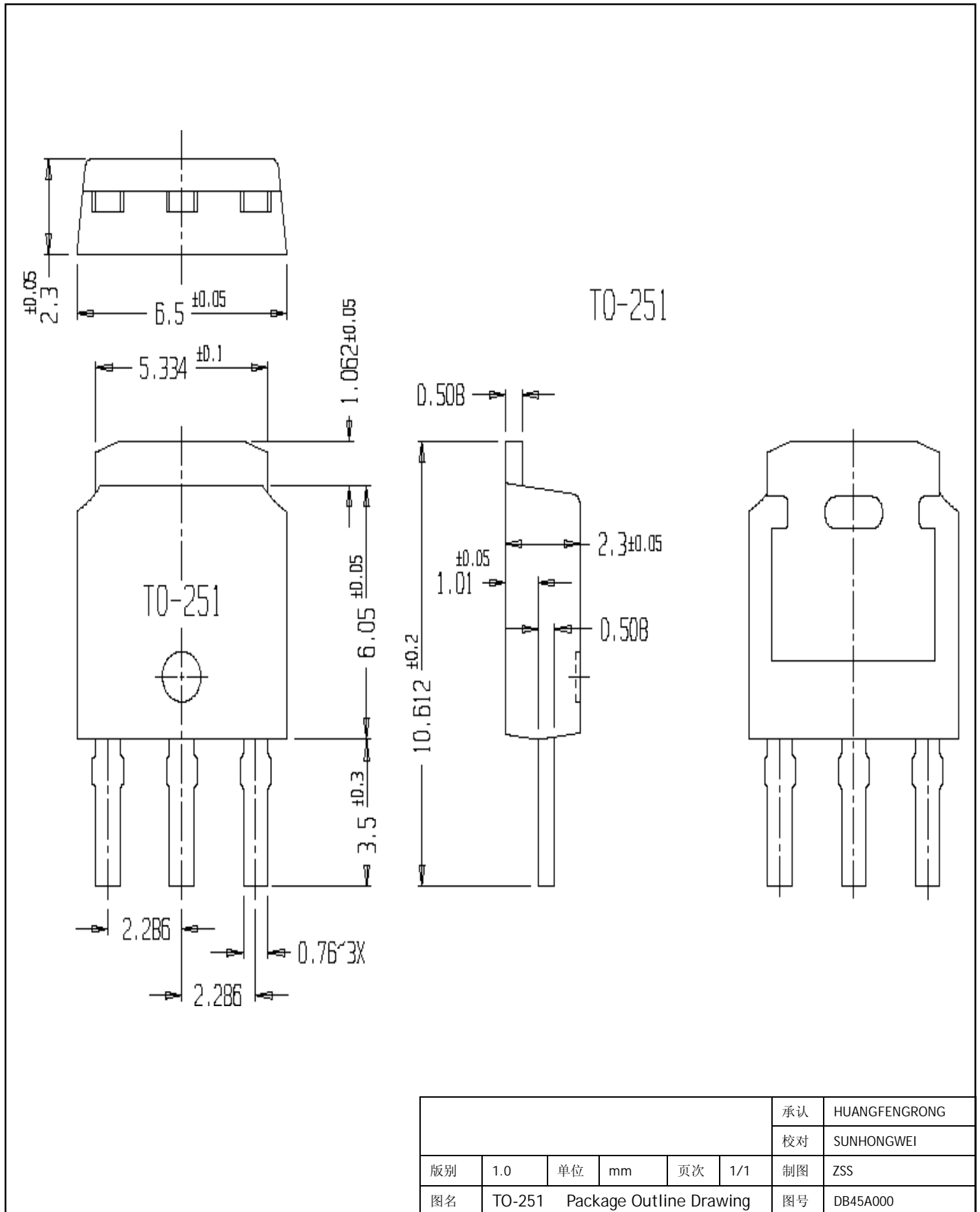
Figure 5. Forward Power Dissipation



TO-252



						承认	HUANGFENGRONG
						校对	SUNHONGWEI
版别	1.0	单位	mm	页次	1/1	制图	ZSS
图名	TO-252 Package Outline Drawing					图号	DB45B000



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